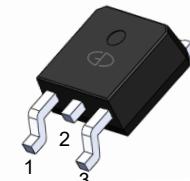


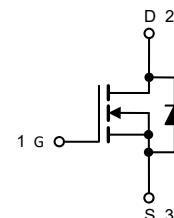
N-Channel 40V (D-S) Power MOSFET

Features

- 100% Avalanche Tested
- Extremely Low Losses with Low FOM $R_{DS(on)} \cdot Q_g$
- RoHS Compliant, Halogen Free, Pb-Free
- AEC-Q101 Qualified
- MSL 1



TO-252 (D-PAK)



Applications

- Automotive systems
- Motors, lamps and solenoid control
- Ultra high performance power switching

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|----------------|-------------|------|
| Drain-Source Voltage | V_{DS} | 40 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current, Continuous $V_{GS}=10\text{V}$ | I_D | 105 | A |
| | | 74 | |
| Drain Current, Pulsed (Note 1) | I_{DM} | 420 | A |
| Single Avalanche Energy (Note 2) | E_{AS} | 246 | mJ |
| Power Dissipation | P_D | 83 | W |
| | | 41 | |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to +175 | °C |

Note 1: Single pulse; $t_p \leq 1\mu\text{s}$.

Note 2: $V_{DD} = 20\text{V}$, $V_{GS} = 10\text{V}$, $L = 0.5\text{mH}$, $R_G = 25\Omega$, starting $T_J = 25^\circ\text{C}$.

Thermal Characteristics

| Parameter | Symbol | Max. | Unit |
|---|------------|------|------|
| Thermal Resistance Junction to Case | R_{thJC} | 1.8 | °C/W |
| Thermal Resistance Junction to Ambient (Note 3) | R_{thJA} | 62.5 | °C/W |

Note 3: Device mounted on 1 square inch FR4 PCB board, with 2oz single-sided copper, in a 25°C still air environment.

| Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted) | | | | | | |
|---|-----------------------------|--|------|------|-----------|------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Drain-Source Breakdown Voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$ | 40 | -- | -- | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$ | -- | -- | 1 | μA |
| Gate Threshold Voltage | $V_{\text{GS}(\text{TH})}$ | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{DS}}=250\mu\text{A}$ | 2 | 2.6 | 4 | V |
| Gate Leakage Current | I_{GSS} | $V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$ | -- | -- | ± 100 | nA |
| Drain-Source On-state Resistance (Note 4) | $R_{\text{DS}(\text{on})}$ | $V_{\text{GS}}=10\text{V}, I_D=20\text{A}$ | -- | 3.1 | 3.8 | $\text{m}\Omega$ |
| Total Gate Charge | Q_g | $V_{\text{GS}(\text{off})}=0\text{V}, V_{\text{GS}(\text{on})}=10\text{V}, V_{\text{DD}}=32\text{V}, I_D=90\text{A}$ | -- | 89 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 52 | -- | |
| Gate-Drain Charge | Q_{gd} | | -- | 15 | -- | |
| Turn-on Delay Time | $t_{\text{d}(\text{on})}$ | $V_{\text{GS}}=10\text{V}, V_{\text{DD}}=20\text{V}, R_L=0.75\Omega, R_G=3\Omega$ | -- | 20 | -- | ns |
| Turn-on Rise Time | t_r | | -- | 18 | -- | |
| Turn-off Delay Time | $t_{\text{d}(\text{off})}$ | | -- | 47 | -- | |
| Turn-off Fall Time | t_f | | -- | 15 | -- | |
| Gate Resistance | R_g | $V_{\text{GS}}=0\text{V}, f=1\text{MHz}, \text{open drain}$ | -- | 1.0 | -- | Ω |
| Input Capacitance | C_{iss} | $V_{\text{GS}}=0\text{V}, V_{\text{DS}}=40\text{V}, f=1\text{MHz}$ | -- | 4800 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 360 | -- | |
| Reverse Transfer Capacitance | C_{rss} | | -- | 277 | -- | |

| Reverse Diode Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted) | | | | | | |
|--|-----------------|--|------|------|------|------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Forward Current, Continuous | I_{SD} | $T_C=25^\circ\text{C}$ | -- | -- | 71 | A |
| Diode Forward Voltage (Note 4) | V_{SD} | $I_F=20\text{A}, V_{\text{GS}}=0\text{V}$ | -- | -- | 1.2 | V |
| Reverse Recovery Time | T_{rr} | $V_R=20\text{V}, I_F=50\text{A}, \frac{dI}{dt}=100\text{ A}/\mu\text{s}$ | -- | 30 | -- | ns |
| Reverse Recovery Charge | Q_{rr} | | -- | 25 | -- | nC |

Note 4: Pulse test; pulse width $\leq 380\mu\text{s}$, duty cycle $\leq 1\%$.

Typical Characteristics Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 - Output Characteristics

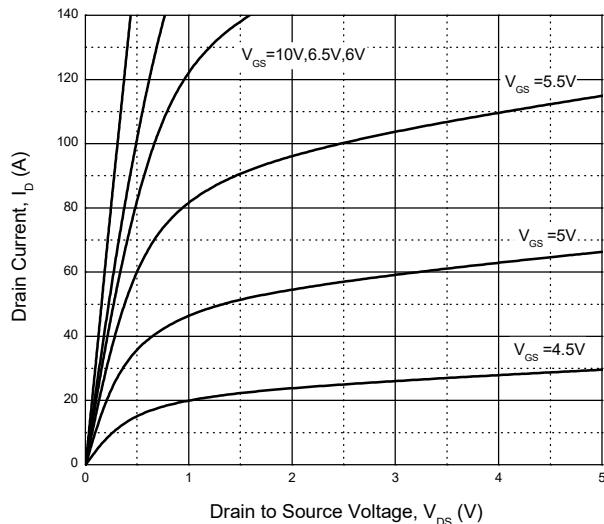


Fig. 2 - Transfer Characteristics

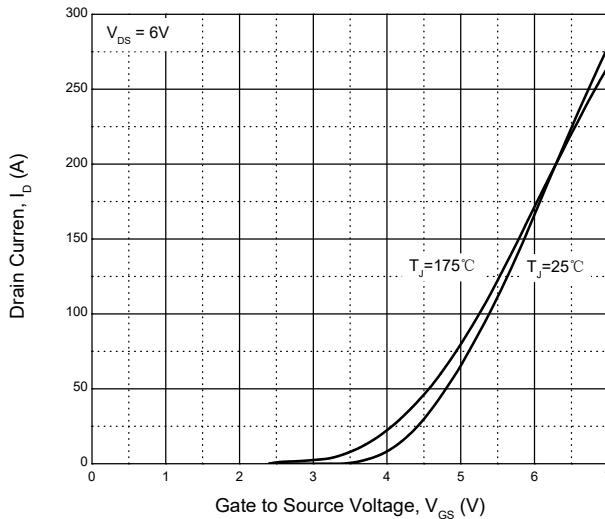


Fig. 3 - Drain-Source On-Resistance

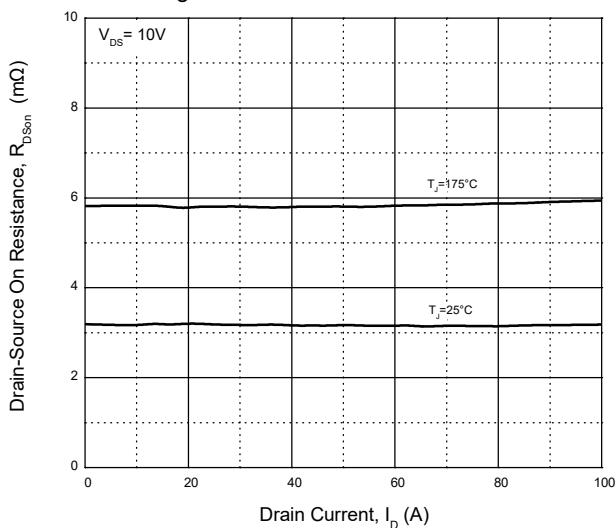


Fig. 4 - Normalized On-Resistance

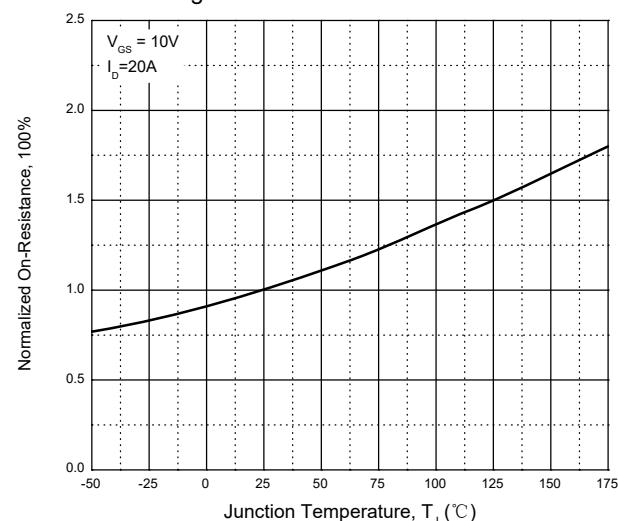


Fig. 5 - Drain-Source On-Resistance

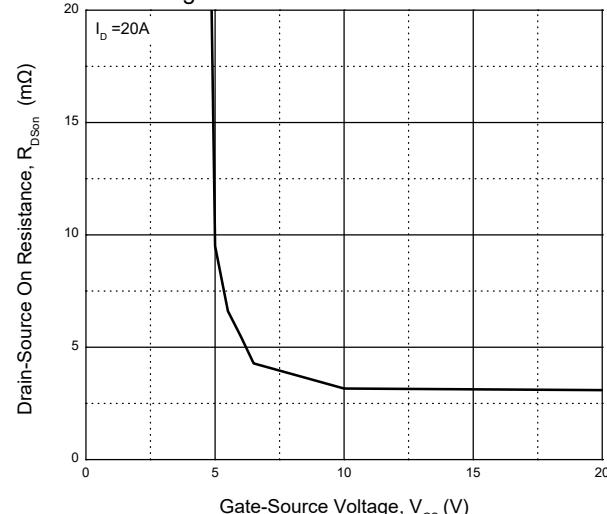
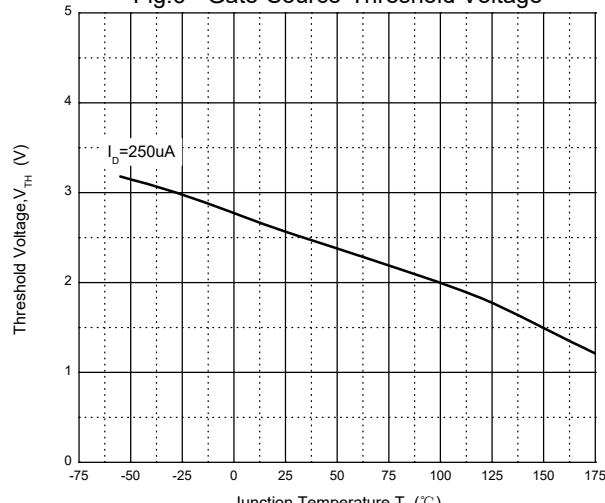
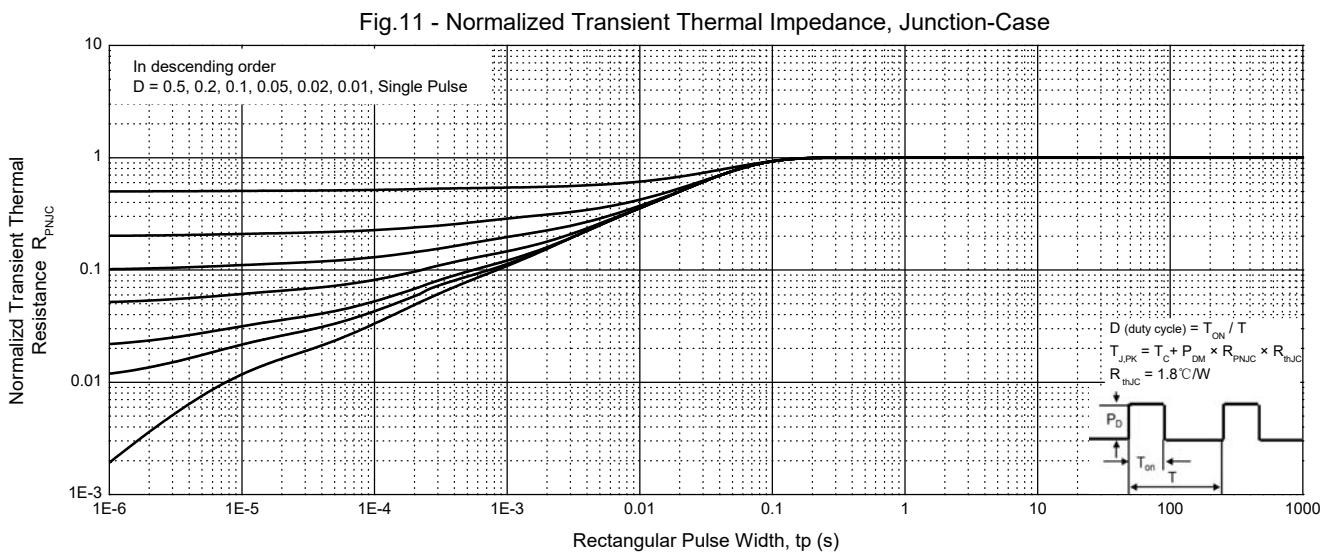
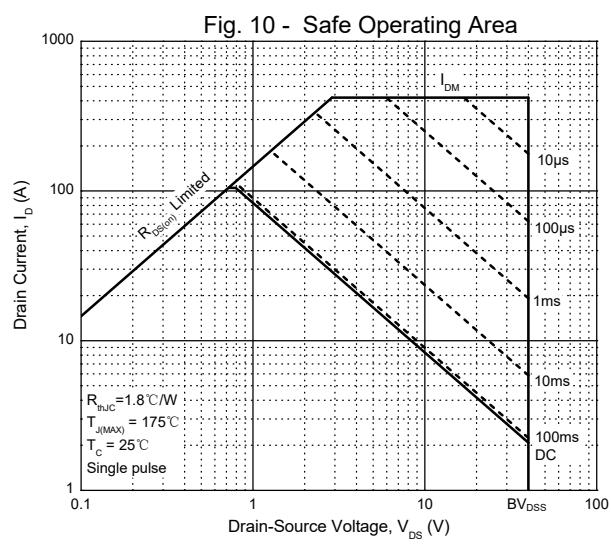
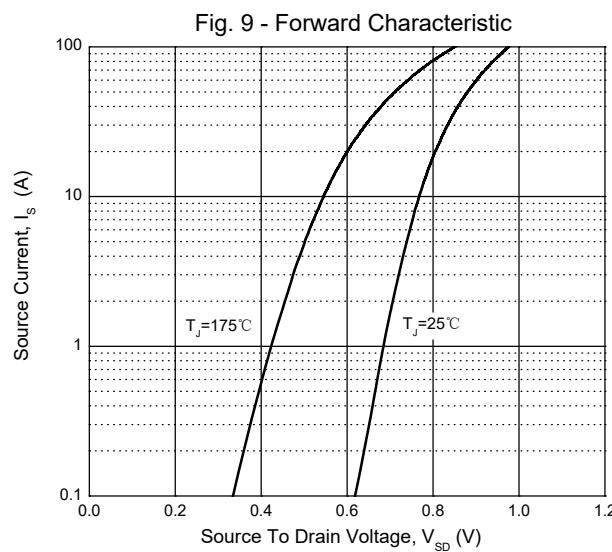
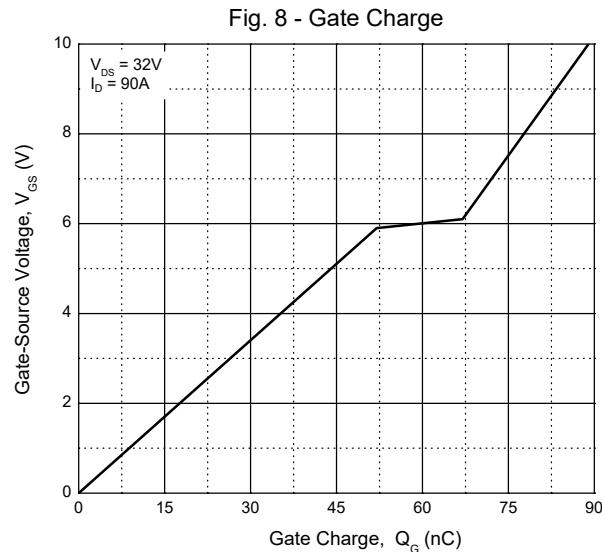
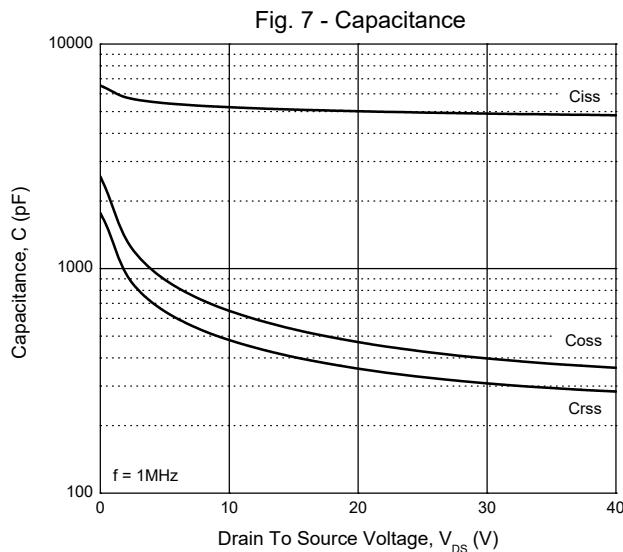


Fig. 6 - Gate-Source Threshold Voltage



Typical Characteristics Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)



Typical Characteristics Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig. 12 - Power Derating

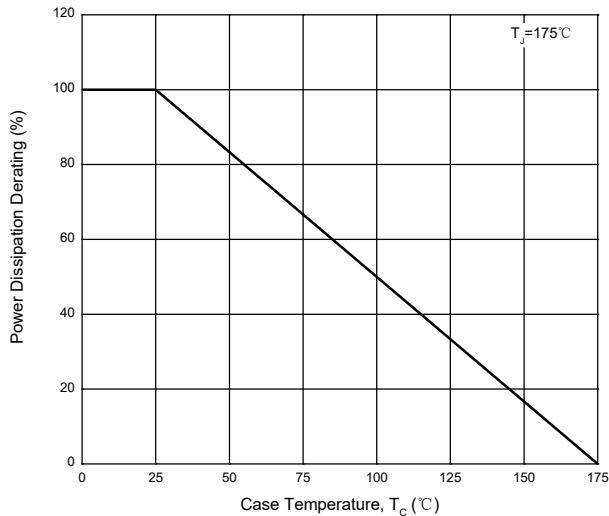
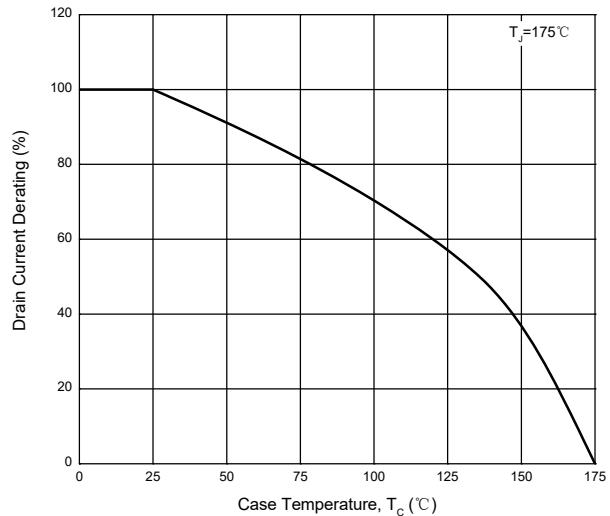
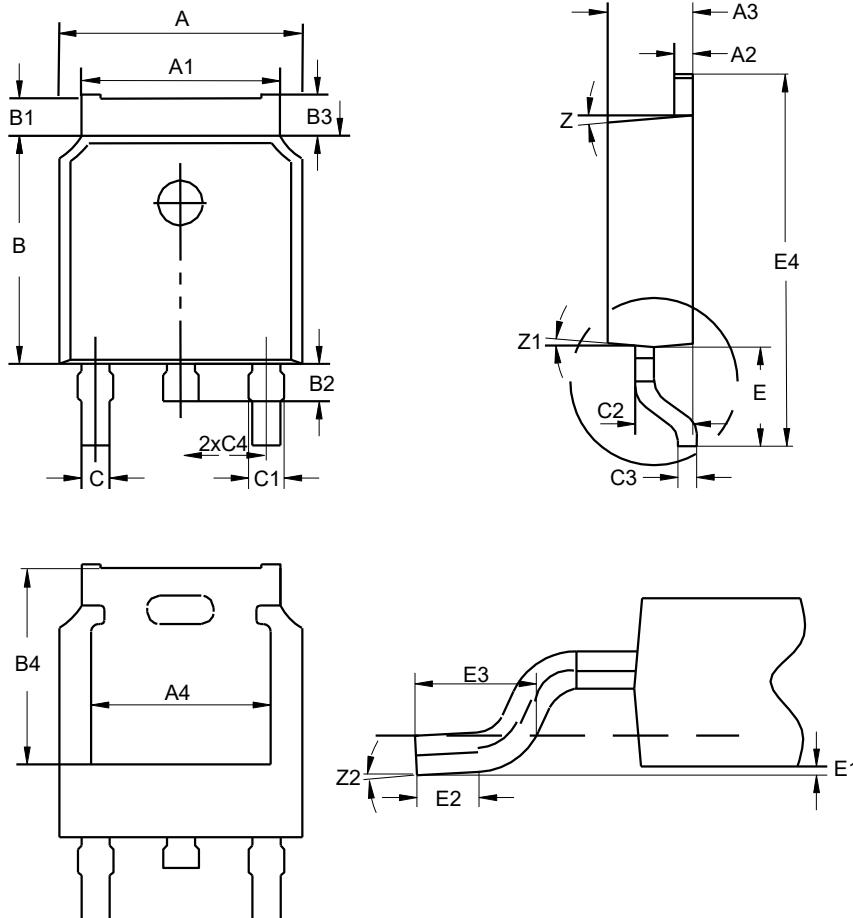


Fig. 13 - Drain Current Derating



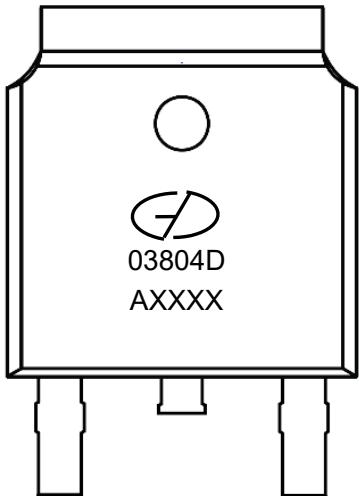
Package Outline Dimensions (Unit: millimeters)

TO-252(D-PAK)



| TO-252 | | | | | | | |
|--------|------|------|------|----|------|------|------|
| | Min. | Nom. | Max. | | Min. | Nom. | Max. |
| A | 6.34 | 6.54 | 6.74 | C2 | 1.34 | 1.54 | 1.74 |
| A1 | 5.2 | 5.3 | 5.4 | C3 | 0.4 | 0.5 | 0.6 |
| A2 | 0.4 | 0.5 | 0.6 | C4 | 2.09 | 2.29 | 2.49 |
| A3 | 2.08 | 2.28 | 2.48 | E | 2.6 | 2.9 | 3.2 |
| A4 | 4.6 | 4.8 | 5.0 | E1 | 0 | - | 0.15 |
| B | 5.8 | 6.1 | 6.4 | E2 | 0.7 | - | - |
| B1 | 0.82 | 1.02 | 1.22 | E3 | 1.3 | 1.6 | 1.9 |
| B2 | 0.8 | 1 | 1.2 | E4 | 9.8 | 10.1 | 10.4 |
| B3 | 0.9 | 1.1 | 1.3 | Z | - | 7° | - |
| B4 | 5.05 | 5.25 | 5.45 | Z1 | - | 7° | - |
| C | 0.66 | 0.76 | 0.86 | Z2 | 0° | - | 10° |
| C1 | 0.75 | 0.95 | 1.15 | - | - | - | - |

Marking Outline



Part Name: AGMN03804D

1. Logo Mark: 
2. P/N Mark: 03804D
3. Date Code: AXXXX

Revision History

| Version | Date | Major Changes |
|---------|------------|------------------|
| Rev.A | 2024.10.28 | Official Release |
| | | |
| | | |

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